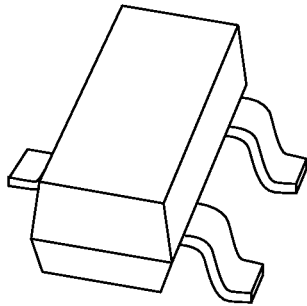


# DATA SHEET



## **BCF29; BCF30** PNP general purpose transistors

Product specification  
Supersedes data of September 1994  
File under Discrete Semiconductors, SC04

1997 May 22

# PNP general purpose transistors

# BCF29; BCF30

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 32 V).

### APPLICATIONS

- Low level, low noise general purpose applications in thick and thin-film circuits.

### DESCRIPTION

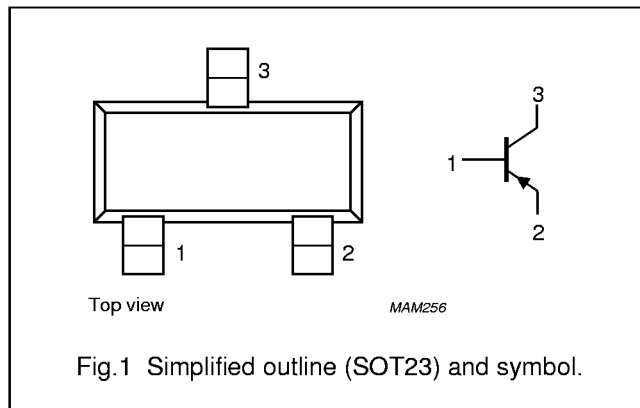
PNP transistor in a SOT23 plastic package.  
NPN complements: BCF32 and BCF33.

### MARKING

TYPE NUMBER	MARKING CODE
BCF29	C7p
BCF30	C8p

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–32	V
$V_{CEO}$	collector-emitter voltage	open base	–	–32	V
$I_{CM}$	peak collector current		–	–200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	250	mW
$h_{FE}$	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$			
	BCF29		120	260	
	BCF30		215	500	
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	MHz

## PNP general purpose transistors

BCF29; BCF30

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–32	V
$V_{CEO}$	collector-emitter voltage	open base	–	–32	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–100	mA
$I_{CM}$	peak collector current		–	–200	mA
$I_{BM}$	peak base current		–	–100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{thj-a}$	thermal resistance from junction to ambient	note 1	500	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

## PNP general purpose transistors

## BCF29; BCF30

**CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -32\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -32\text{ V}; T_j = 100\text{ °C}$	–	–	–10	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
$h_{FE}$	DC current gain BCF29 BCF30	$I_C = -10\text{ }\mu\text{A}; V_{CE} = -5\text{ V}$	–	90	–	
			–	150	–	
$h_{FE}$	DC current gain BCF29 BCF30	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	120	–	260	
			215	–	500	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–80	–300	mV
		$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}$	–	–150	–	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–720	–	mV
		$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}$	–	–810	–	mV
$V_{BE}$	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	–600	–	–750	mV
$C_c$	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	4.5	–	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	1	4	dB

PNP general purpose transistors

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23

